NSN 5961-01-198-1913

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view Online at https://aerobasegroup.com/hsn/5961-01-196-1915
Inclosure Material:
Metal
Overall Length:
1.253 inches
Overall Diameter:
0.505 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-4
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Overall Width Across Flats:
Between 0.423 inches and 0.438 inches
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
12.0 regulator voltage
Voltage Tolerance In Percent:
-5.0/+5.0
Current Rating Per Characteristic:
210.00 milliamperes source cutoff current horsepower metric
Power Rating Per Characteristic:
10.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Precious Material And Location:
Terminal surface option silver or gold
Precious Material:
Gold or silver
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:

Specification Data:

81349-mil-s-19500/124 government specification

1 tab, solder lug and 1 threaded stud

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N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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